

SOT23 SILICON EPITAXIAL SCHOTTKY BARRIER SINGLE AND DUAL DIODES

BAT54

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PARTMARKING DETAILS

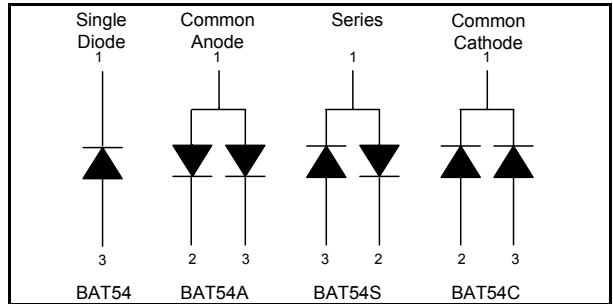
Single Diode – L4Z
Common Anode – L42
Series – L43
Common Cathode – L44

FEATURES

Low V_F
High current capability

APPLICATIONS

P.S.U.
Mobile telecomms. & SCSI



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Continuous Reverse Voltage	V_R	30	V
Forward Current	I_F	200	mA
Forward Voltage	V_F	400	mV
Power Dissipation at $T_{amb}=25^\circ\text{C}$	P_{tot}	330	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Reverse Breakdown Voltage	$V_{(BR)R}$	30			V	$I_R=10\text{mA}$
Forward Voltage	V_F		500	240 320 400 500 1000	mV mV mV mV mV	$I_F=0.1\text{mA}$ $I_F=1\text{mA}$ $I_F=10\text{mA}$ $I_F=30\text{mA}$ $I_F=100\text{mA}$
Reverse Current	I_R			4	μA	$V_R=25\text{V}$
Diode Capacitance	C_D			10	pF	$f=1\text{MHz}, V_R=1\text{V}$
Reverse Recover Time	t_{rr}			5	ns	switched from $I_F=10\text{mA}$ to $I_R=10\text{mA}$ $R_L=100\Omega$, Measured at $I_R=1\text{mA}$